

DUAL BIPOLAR OPERATIONAL AMPLIFIERS

AZ4558C

Pin Configuration

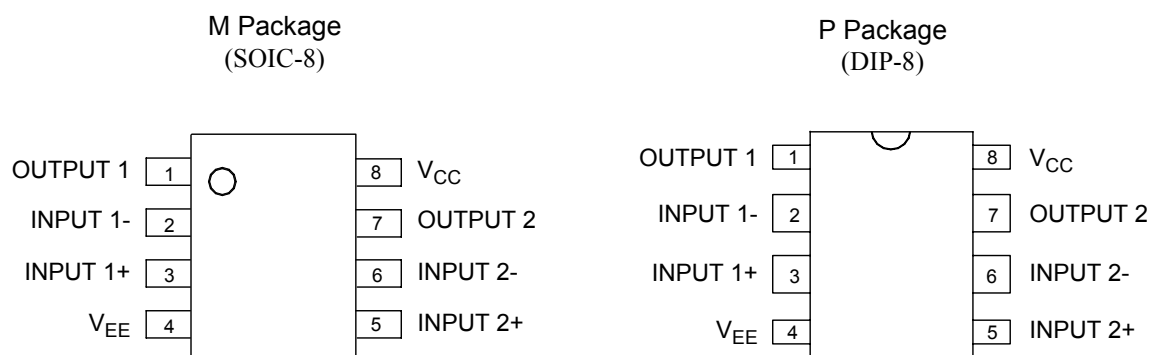


Figure 2. Pin Configuration of AZ4558C (Top View)

Functional Block Diagram

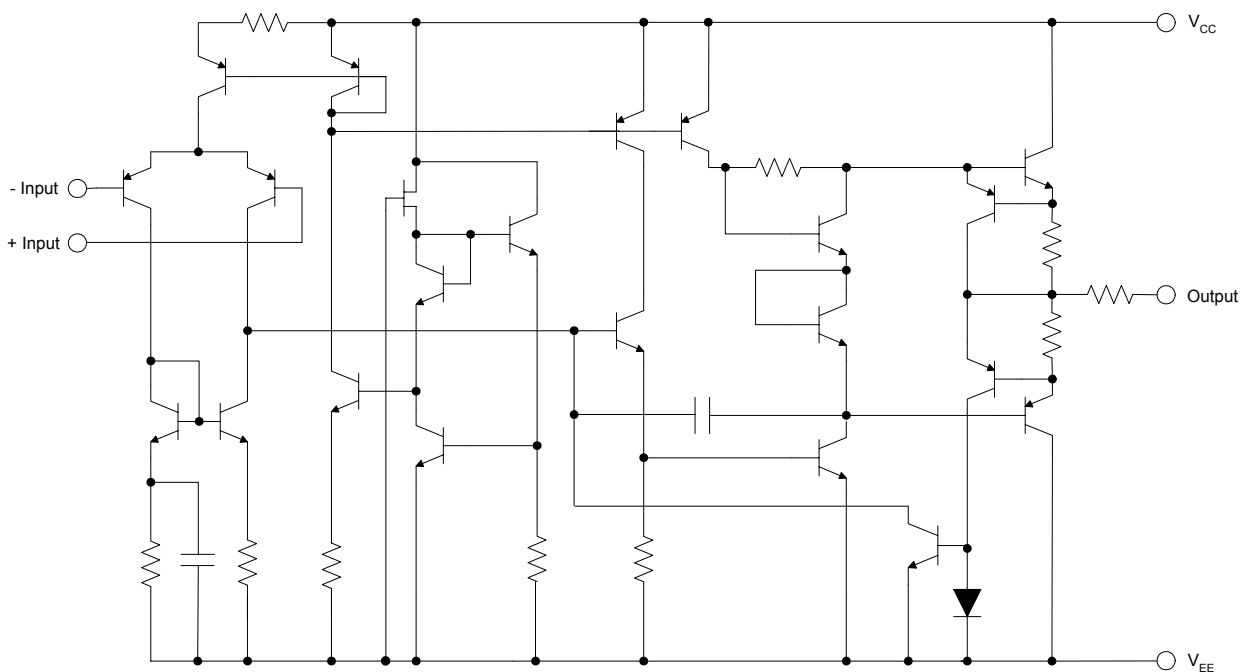
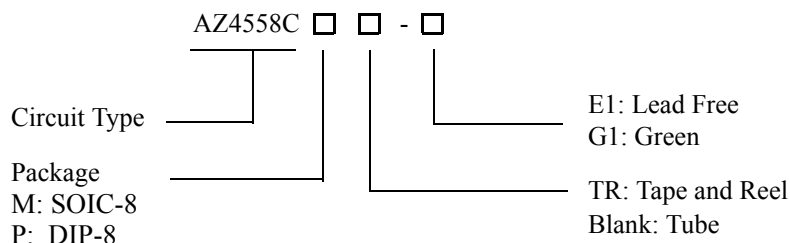


Figure 3. Functional Block Diagram of AZ4558C (Each Amplifier)

**DUAL BIPOLAR OPERATIONAL AMPLIFIERS****AZ4558C****Ordering Information**

Package	Temperature Range	Part Number		Marking ID		Packing Type
		Lead Free	Green	Lead Free	Green	
SOIC-8	-40 to 85°C	AZ4558CM-E1	AZ4558CM-G1	4558CM-E1	4558CM-G1	Tube
		AZ4558CMTR-E1	AZ4558CMTR-G1	4558CM-E1	4558CM-G1	Tape & Reel
DIP-8	-40 to 85°C	AZ4558CP-E1	AZ4558CP-G1	AZ4558CP-E1	AZ4558CP-G1	Tube

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant. Products with "G1" suffix are available in green packages.

Absolute Maximum Ratings (Note 1)

Parameter	Symbol	Value		Unit
Supply Voltage	V _{CC}	+20		V
	V _{EE}	-20		
Input Voltage	V _I	±15		V
Differential Input Voltage	V _{ID}	±30		V
Operating Junction Temperature	T _J	150		°C
Storage Temperature Range	T _{STG}	-65 to 150		°C
Lead Temperature (Soldering 10s)	T _L	260		°C
Power Dissipation	P _D	DIP	800	mW
		SOIC	500	mW

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Min	Max	Unit
Supply Voltage	± 2	± 18	V
Operating Temperature Range	-40	85	°C

**DUAL BIPOLAR OPERATIONAL AMPLIFIERS****AZ4558C****Electrical Characteristics**Operating Conditions: $V_{CC}=+15V$, $V_{EE}=-15V$, $T_A=25^{\circ}C$, unless otherwise specified.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input Offset Voltage	V_{IO}			1	5	mV
Input Offset Current	I_{IO}	$V_{CM}=0V$		10	100	nA
Input Bias Current	I_{IB}	$V_{CM}=0V$		70	400	nA
Large Signal Voltage Gain	A_{VD}	$R_L=2K\Omega$, $V_O=\pm 10V$	85	100		dB
Supply Voltage Rejection Ratio	SVR	$R_S \leq 10K\Omega$	80	100		dB
Supply Current	I_{CC}	All Amplifiers, No Load		2.5	4.5	mA
Input Common Mode Voltage Range	V_{ICM}		± 12			V
Common Mode Rejection Ratio	CMRR	$R_S \leq 10K\Omega$	70	95		dB
Output Voltage Swing	V_O	$R_L \geq 10K\Omega$	± 12	± 14		V
		$R_L \geq 2K\Omega$	± 10	± 13		
Slew Rate	SR	$V_I=\pm 10V$, $R_L=2K\Omega$, $C_L=100pF$, unity gain		1.8		V/ μs
Rise Time	T_R	$V_I=\pm 20mV$, $R_L=2K\Omega$, $C_L=100pF$, unity gain		0.3		μs
Overshoot	K_{OV}	$V_I=\pm 20mV$, $R_L=2K\Omega$, $C_L=100pF$, unity gain		15		%
Input Resistance	R_I			0.5		$M\Omega$
Output Resistance	R_O			45		Ω
Unity Gain Bandwidth	B	Gain=0dB		2.8		MHz
Gain Bandwidth Product	GBWP	$V_I=\pm 10mV$, $R_L=2K\Omega$, $C_L=100pF$, $f=10KHz$		5.5		MHz
Total Harmonic Distortion Plus Noise	THD+N	$f=1KHz$, $A_V=6dB$, $R_L=10K\Omega$, $V_O=1V_{RMS}$		0.002		%
Equivalent Input Noise Voltage Density	e_N	$R_S=100\Omega$, $f=1KHz$		10		$\frac{nV}{\sqrt{Hz}}$
Output Current	I_{SINK}	$V=-1V$, $V+=0V$, $V_O=2V$		60		mA
	I_{SOURCE}	$V+=1V$, $V-=0V$, $V_O=2V$		35		
Thermal Resistance (Junction to Case)	θ_{JC}	DIP-8		55		$^{\circ}C/W$
		SOIC-8		81		



Typical Performance Characteristics

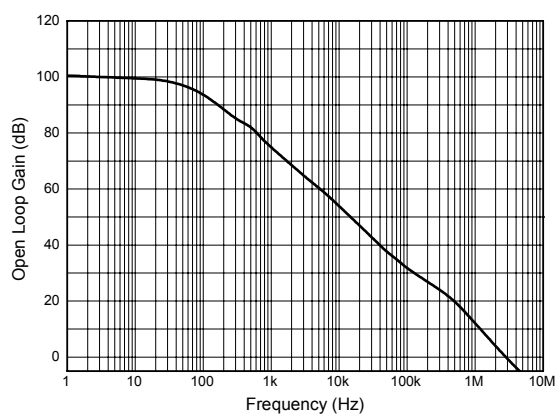


Figure 4. Open Loop Voltage Gain vs. Frequency

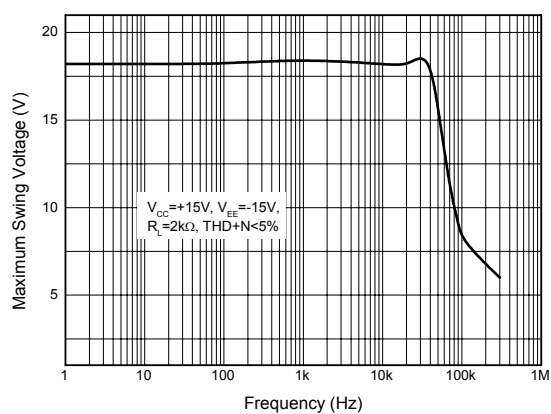


Figure 5. Maximum Output Voltage Swing vs. Frequency

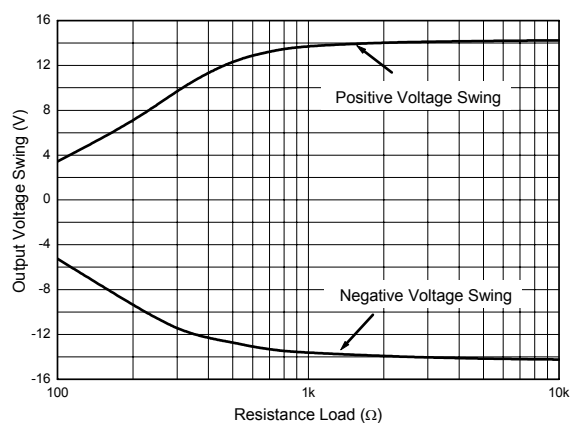


Figure 6. Maximum Output Voltage Swing vs. Load Resistance

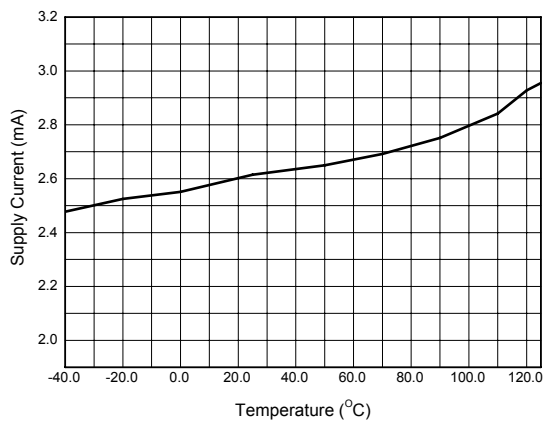


Figure 7. Supply Current vs. Temperature

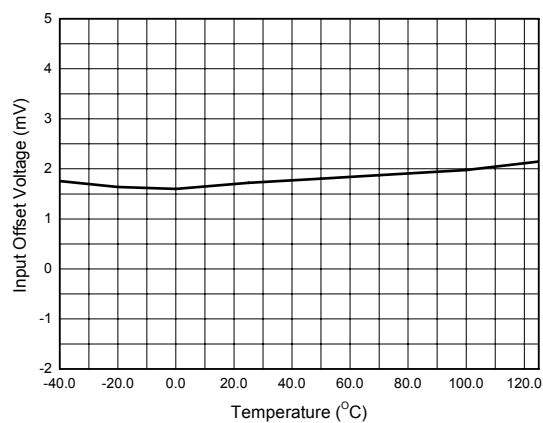
**Typical Performance Characteristics (Continued)**

Figure 8. Input Offset Voltage vs. Temperature

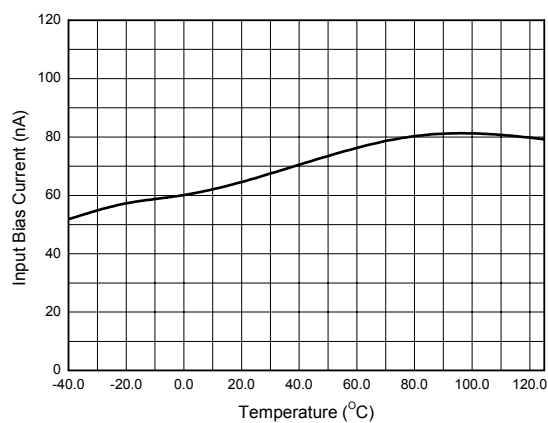


Figure 9. Input Bias Current vs. Temperature

Typical Application

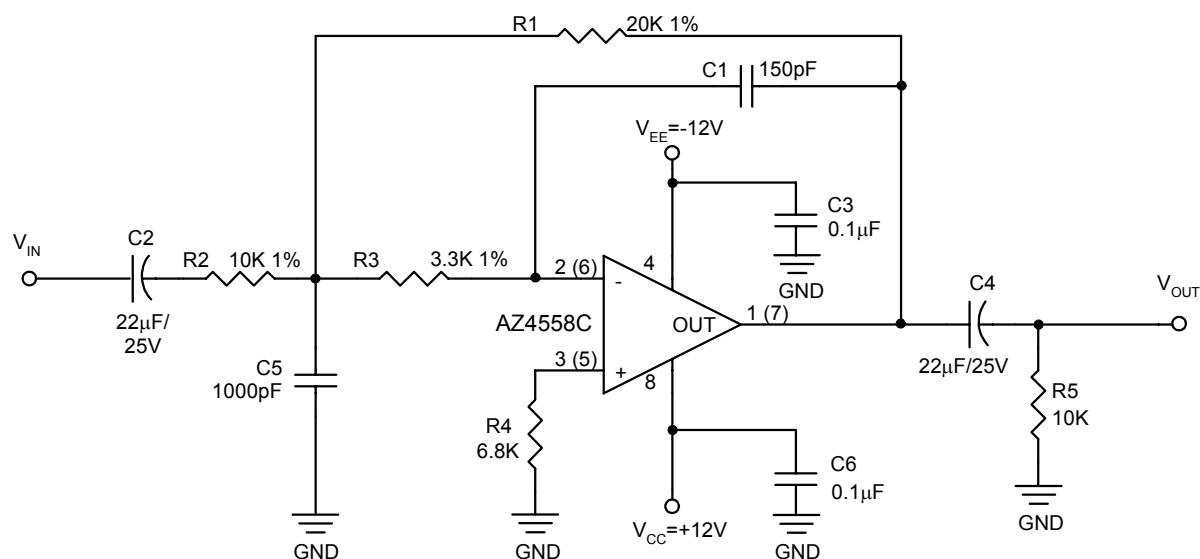


Figure 10. Typical Application of AZ4558C in Audio 2nd Order Low Pass Filter
($f_O=50.6$ kHz, $Q=0.7015$, Input impedance=10K, Gain=6dB, Group delay=4.48 μ s)

**AZ4558C**

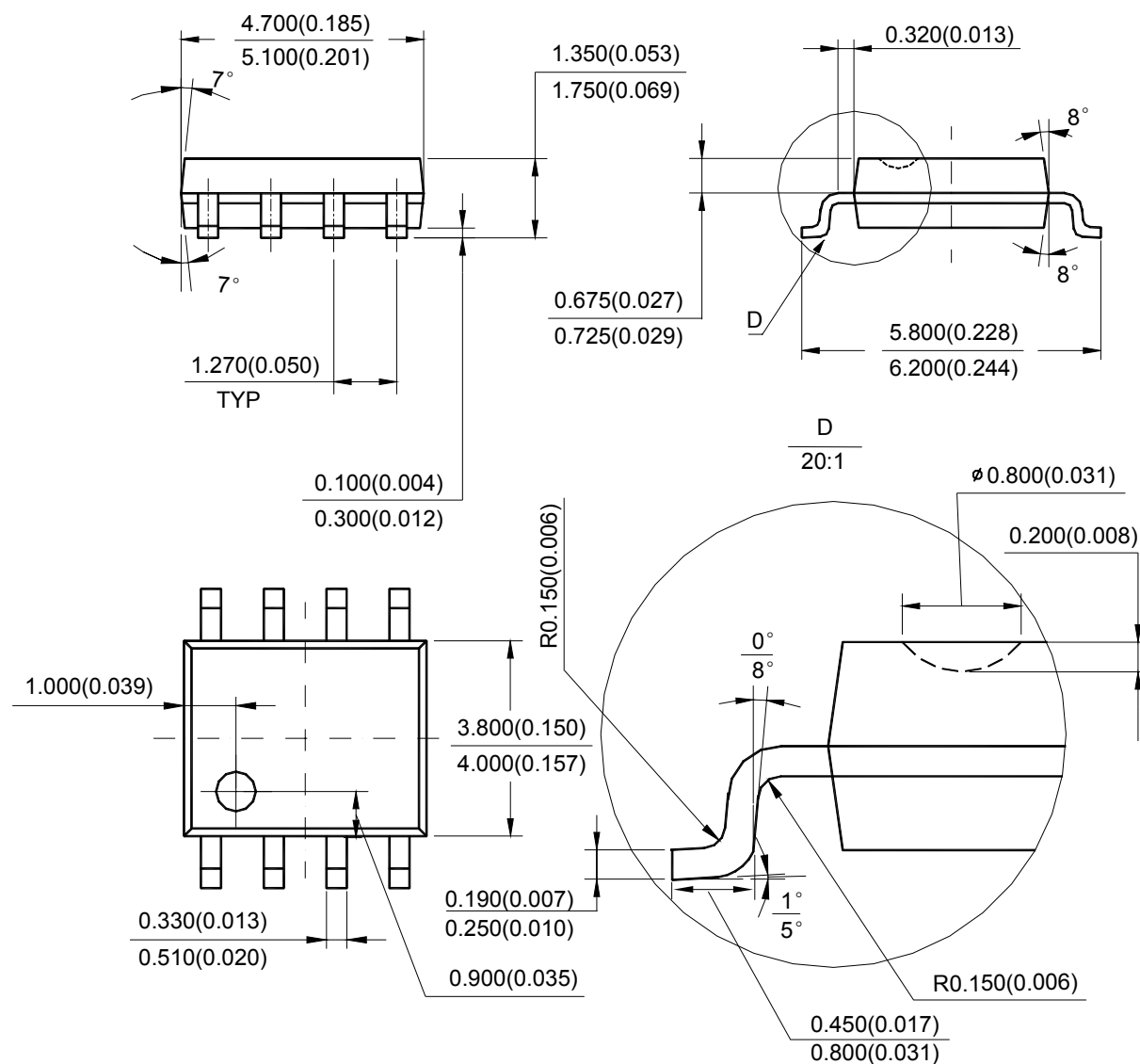
DIP-8

Unit: mm(inch)



**AZ4558C****SOIC-8**

Unit: mm(inch)



Note: Eject hole, oriented hole and mold mark is optional.



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